WHAT IS CLAIMED IS:

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 A device which has a semiconductor device and a micromachine, comprising:

a semiconductor layer on which the semiconductor device is formed; and

a substrate on which the micromachine is formed,
wherein said semiconductor layer and substrate
are stacked, and said semiconductor layer is obtained
by separating, at a separation layer, a member which
has the separation layer under said semiconductor
layer.

2. A device which has a semiconductor device and a micromachine, comprising:

a semiconductor layer on which the semiconductor 15 device is formed; and

a substrate on which the micromachine is formed, wherein said semiconductor layer has a first surface and a second surface, the first surface is bonded to said substrate directly or through a bonding layer, and the second surface adjoins a layer whose structure is more fragile than said semiconductor layer.

- 3. The device according to claim 2, wherein the layer having the fragile structure includes one of a porous layer and an ion-implanted layer.
- 4. A device which has a semiconductor device and a micromachine, comprising:

a semiconductor layer on which the semiconductor device is formed; and a substrate on which the micromachine is formed, wherein said semiconductor layer and substrate

- 5 are stacked, and said semiconductor layer is formed by epitaxial growth.
 - 5. The device according to claim 4, wherein said semiconductor layer has a first surface and a second surface, the first surface is bonded to said substrate directly or through a bonding layer, and the second surface is bonded to an insulator directly or through a bonding layer, or adjoins the insulator.
 - 6. The device according to claim 2, wherein the bonding layer includes one of an adhesive and an adhesion layer.

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- 7. A device which has a semiconductor device and a micromachine, comprising:
- a semiconductor layer on which the semiconductor device is formed; and
- a substrate on which the micromachine is formed, wherein said semiconductor layer and substrate are stacked, and said semiconductor layer has a thickness of not more than 50 μ m.
- 8. A device which has a semiconductor device and a25 micromachine, comprising:
 - a semiconductor layer on which the semiconductor device is formed; and

a substrate on which the micromachine is formed, wherein said semiconductor layer and substrate are stacked, and said semiconductor layer has a thickness of not more than 30 μ m. 5 9. The device according to claim 1, wherein the micromachine includes at least one of a switch, a variable condenser, and an inductor. 10. The device according to claim 1, wherein a semiconductor circuit is formed on said semiconductor 10 layer, and the semiconductor circuit and micromachine comprise at least part of a radio communication device. 11. A substrate comprising: a semiconductor layer on which a circuit is formed; and 15 an antenna substrate on which antennas are formed, wherein said semiconductor layer and antenna substrate are bonded together, and said semiconductor layer is formed by separating, at a separation layer, a 20 substrate which includes the separation layer. 12. The substrate according to claim 11, wherein said semiconductor layer has a film thickness of not more than 50 μ m. 13. The substrate according to claim 11, wherein said 25 semiconductor layer has a film thickness of not more than 30 μ m. 14. The substrate according to claim 11, further - 47 -

comprising a bonding layer which bonds together said semiconductor layer and antenna substrate.

- 15. The substrate according to claim 14, wherein said bonding layer is an adhesive.
- 5 16. The substrate according to claim 11, wherein the antennas are spiral antenna coils.
 - 17. The substrate according to claim 11, wherein the circuit is electrically connected to the antennas and uses the antennas to transmit and receive radio waves.
- 10 18. A method of manufacturing a device which has a semiconductor device and a micromachine, comprising:

a step of preparing a member which has a semiconductor layer and a separation layer and in which the semiconductor layer is arranged on the separation layer;

a step of preparing a substrate on which the micromachine is formed; and

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a step of bonding a side of the member having the semiconductor layer to the substrate directly or through a bonding layer to manufacture a bonded substrate stack.

- 19. The method according to claim 18, further comprising a step of separating the bonded substrate stack at the separation layer.
- 25 20. The method according to claim 18, wherein in the step of preparing the member, the separation layer is formed by anodization or is formed by ion implantation.

- 21. The method according to claim 18, wherein the bonding layer includes one of an adhesive and an adhesion layer.
- 22. The method according to claim 18, wherein
 the step of preparing the substrate further
 comprises a step of preparing an antenna substrate on
 which an antenna is formed, and

the step of manufacturing the bonded substrate stack further comprises a step of bonding the side of the member having the semiconductor layer to the antenna substrate directly or through a bonding layer to manufacture a bonded substrate stack.

23. A method of manufacturing a substrate, comprising:

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a step of preparing a member which has a semiconductor layer and a separation layer and in which the semiconductor layer is arranged on the separation layer;

a step of preparing an antenna substrate on which
20 an antenna is formed; and

a step of bonding a side of the member having the semiconductor layer to the antenna substrate directly or through a bonding layer to manufacture a bonded substrate stack.

25 24. The method according to claim 23, further comprising a step of separating the bonded substrate stack at the separation layer.